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Large Area Photodetector Development: Project Status

*Bob Wagner, Project Physicist
for LAPD Collaboration*

*Work on Timing Detectors, Clermont-Ferrand
28 Jan 2010*

The Large Area Photodetector Collaboration

Received first funds in August, 2009

Many others have joined since original proposal:

- Argonne HEP - Slade Jokela, Seon Woo Lee, Bob Wagner
 - Argonne Nuclear Science - Dean Walters
 - Argonne Energy Systems - Qing Peng, Anil Mane
 - Argonne Materials Science - Thomas Proslie
 - U. Chicago - Erik Oberla, Sam Meehan, Hervé Grabas
 - SSL - Sharon Jelinsky, Jason McPhate
 - U. Illinois, Chicago - Kathleen Broughton
- plus certainly others I overlooked

The Development of Large-Area Fast Photo-detectors

April 15, 2009

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University of Hawaii, 2505 Correa Road, Honolulu, HI, 96822

Robert Abrams, Valentin Ivanov, Thomas Roberts
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Oswald Siegmund, Anton Tremsin
Space Sciences Laboratory, University of California, Berkeley, CA 94720

Dmitri Routkevitch
Synkera Technologies Inc., Longmont, CO 80501

David Forbush, Tianchi Zhao
Department of Physics, University of Washington, Seattle, WA 98195

¹ Joint appointment Argonne National Laboratory and Enrico Fermi Institute, University of Chicago

LAPD Project Scope

Develop and Fabricate Microchannel Plate Photodetector Incorporating:

- 20×20 cm² active area
- High quantum efficiency photocathode --- $\geq 25\%$
 - Alkali, multialkali
 - “III-V” materials, e.g. GaAs, GaN
- Novel inexpensive MCP substrate
 - Bare Glass Capillary Substrates - borofloat glass
 - Anodic Aluminum Oxide (AAO) - ceramic
- Pore activation via Atomic Layer Deposit (ALD)
 - Separate material for resistive and emissive layer
 - Evaporative metallization for high voltage electrical contact
- Customized anode readout
 - Double-ended strip line readout for picosecond timing
 - Conventional pad readout for energy and/or coarse spatial location
 - *Gamma-ray telescope camera (see K. Byrum talk)*
 - *Dual readout calorimeters*
 - *Medical imaging?*
- Possibly novel front-end electronics, e.g. picosecond timing ASIC chip (see J-F. Genat talk)
- Design by vetted and tuned simulation

Photocathode Development

- Initial photocathode will be bialkali: Na-K-Sb
 - Univ. California - Space Science Lab has many years experience with fabrication
 - Current facilities not adequate for 8"×8" photocathode fabrication (and vacuum assembly of MCP-PMT)
- First year milestone is upgrade of SSL facilities for large area MCP-PMT assembly
- Need to study/develop large area photocathode deposition technique
 - Largest photocathode to be made by evaporation deposition on flat glass
- Photocathode development at Argonne beginning
 - Interest in III-V materials for X-ray source work
 - Bi/multialkali work also
 - Plan for Argonne facility near completion
- First make working photocathode, then worry about increasing QE
 - Small sample work on Borofloat 33 & 270 glass starting at SSL

Glass Substrate Status

- Glass substrate development, fabrication, slicing by Incom, Inc. (Charlton, MA, USA)
- Disk development substrates in production
 - 32.8mm diameter
 - 40 μ m pore size L/D=40 samples on hand at Argonne. Used in first ALD coatings
 - 20 μ m pore L/D=60 pieces being produced and delivered now. This is our default working size
- 8"×8" 20 μ m pore fabrication starting at Incom.
- All substrate pores have 8° bias



32.8mm 20 μ m pore L/D=60 disks

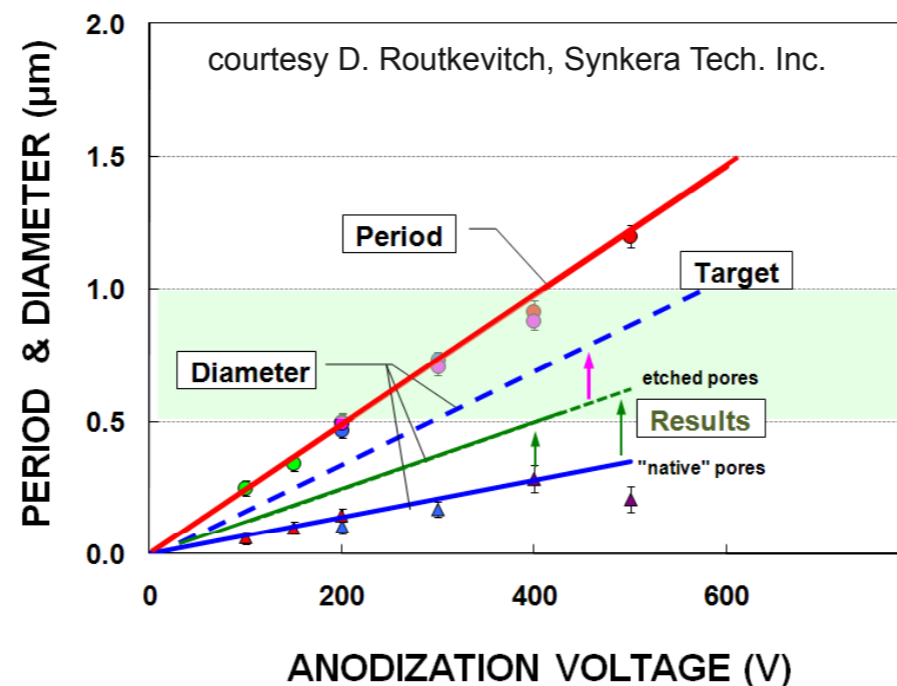


photo credit: Jason McPhate, SSL

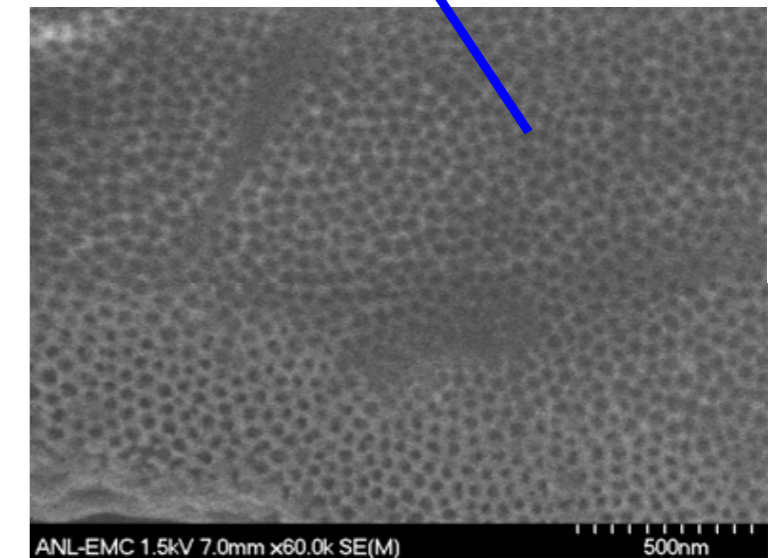
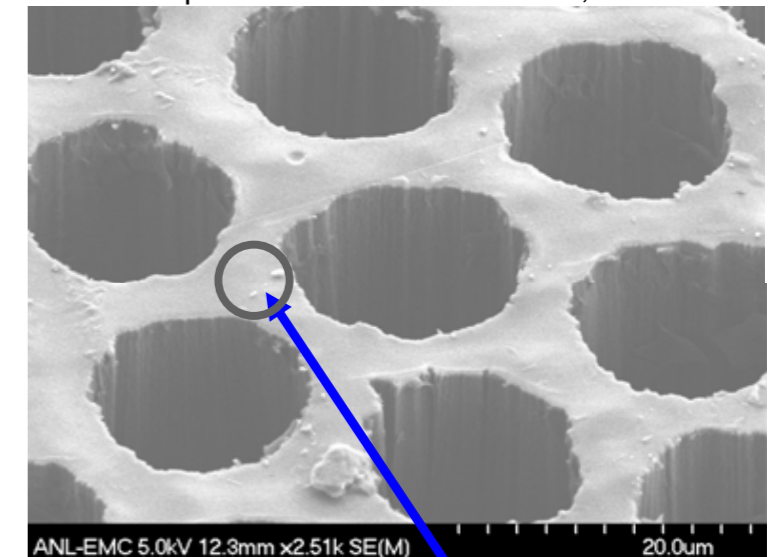
Anodic Aluminum Oxide (AAO)

- Potential inexpensive method to produce pore structure
 - Electrochemical etching of pure Al
 - Pores form self-organizing structure
- Maximum pore size limited $\ll 1 \mu\text{m}$. No bias angle.
- Development at Argonne (Wang/Lee)
 - Etch pore size 20-40nm
 - Use photolithography to enlarge pores to 2-10 μm
 - Small initial pores produce straight wall larger pores
- Synkera Technologies, Colorado (Routkevitch)
 - Produce larger pores directly with larger anodization voltage

Pore Size/Spacing vs Anodization Voltage
Synkera AAO development



SEM photo credit: Seon Woo Lee, ANL

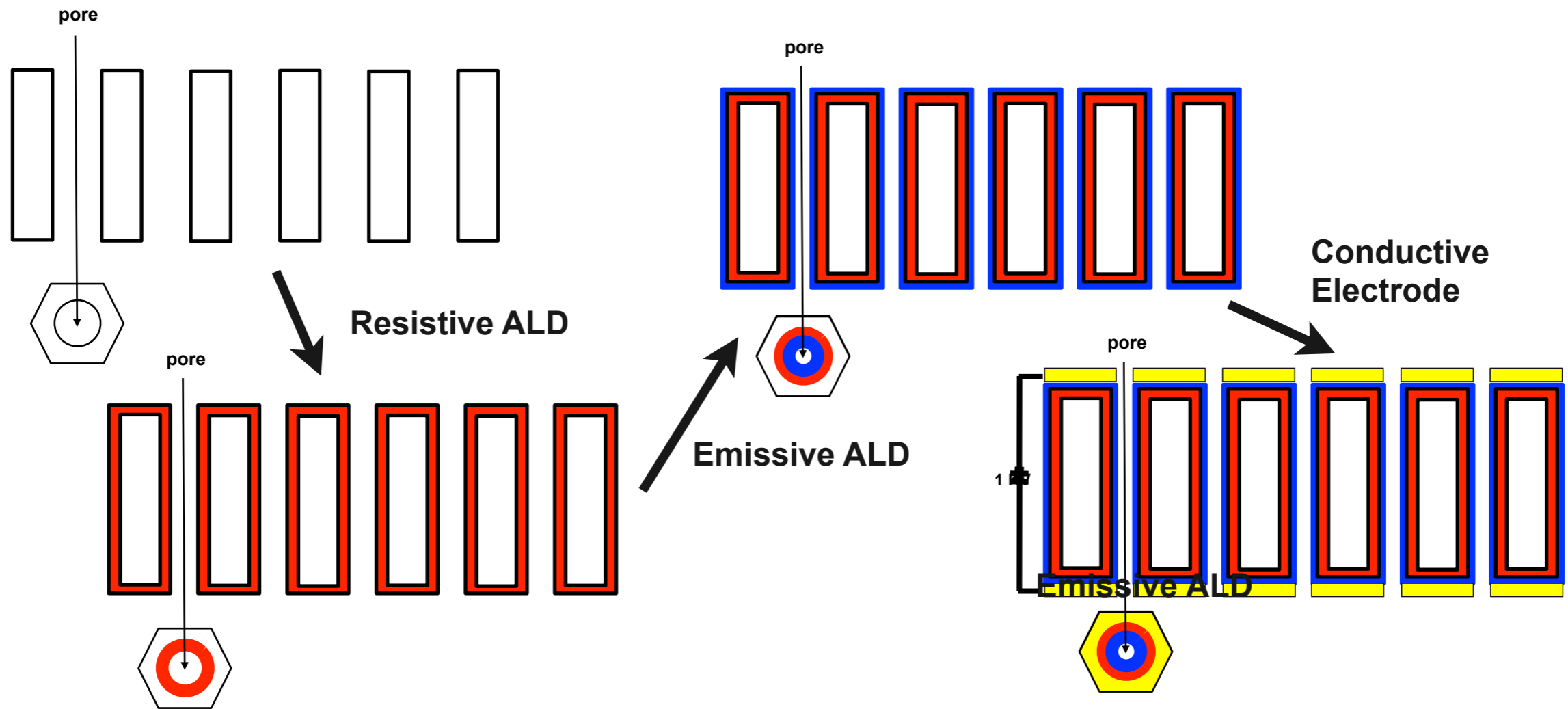
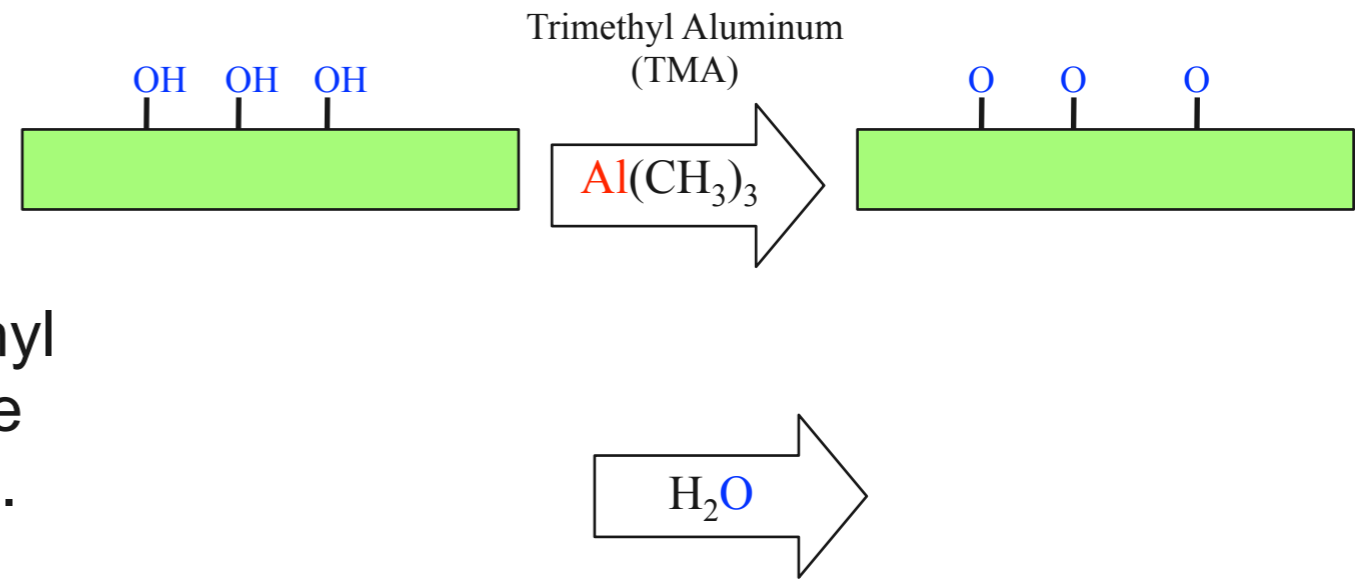


AAO development at Argonne

Pore Activation via Atomic Layer Deposition (ALD)

Example:

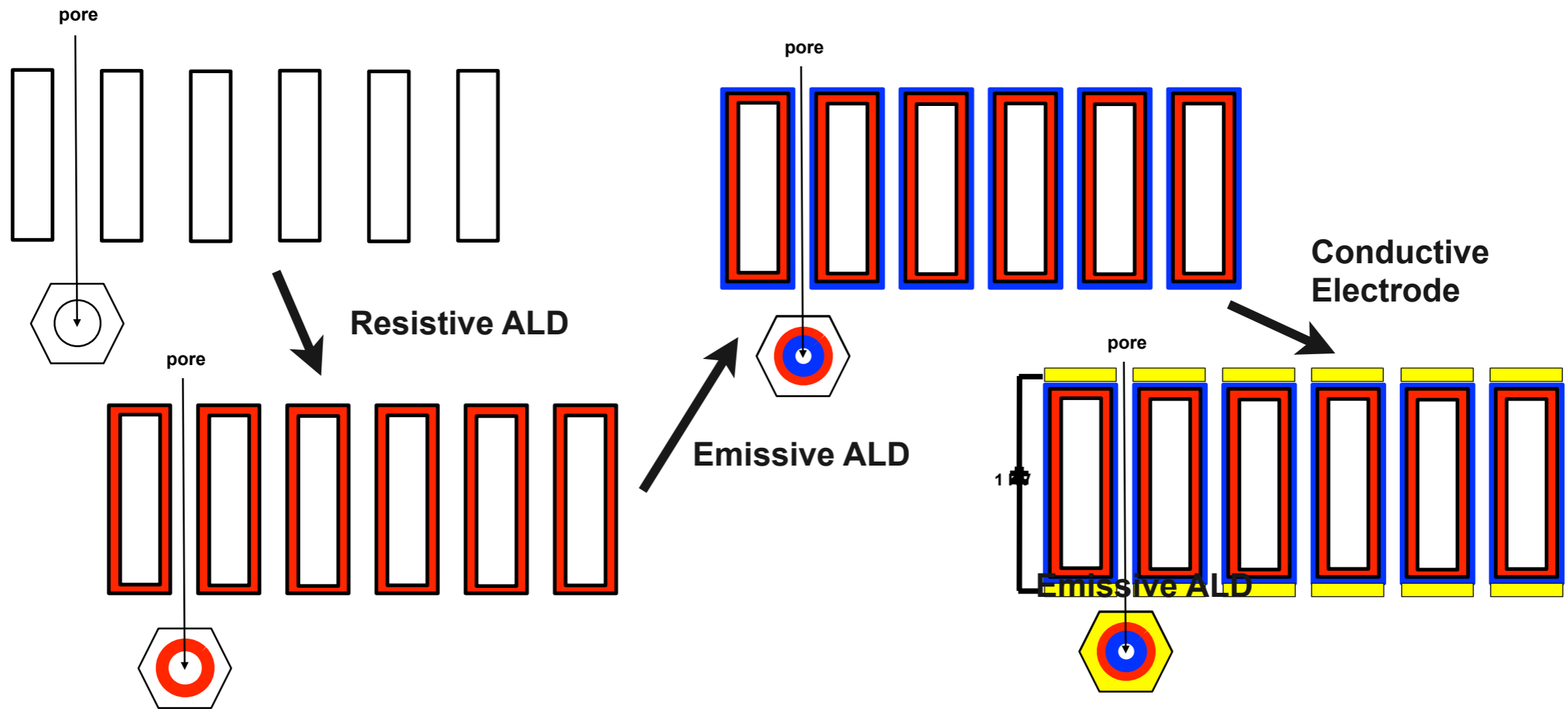
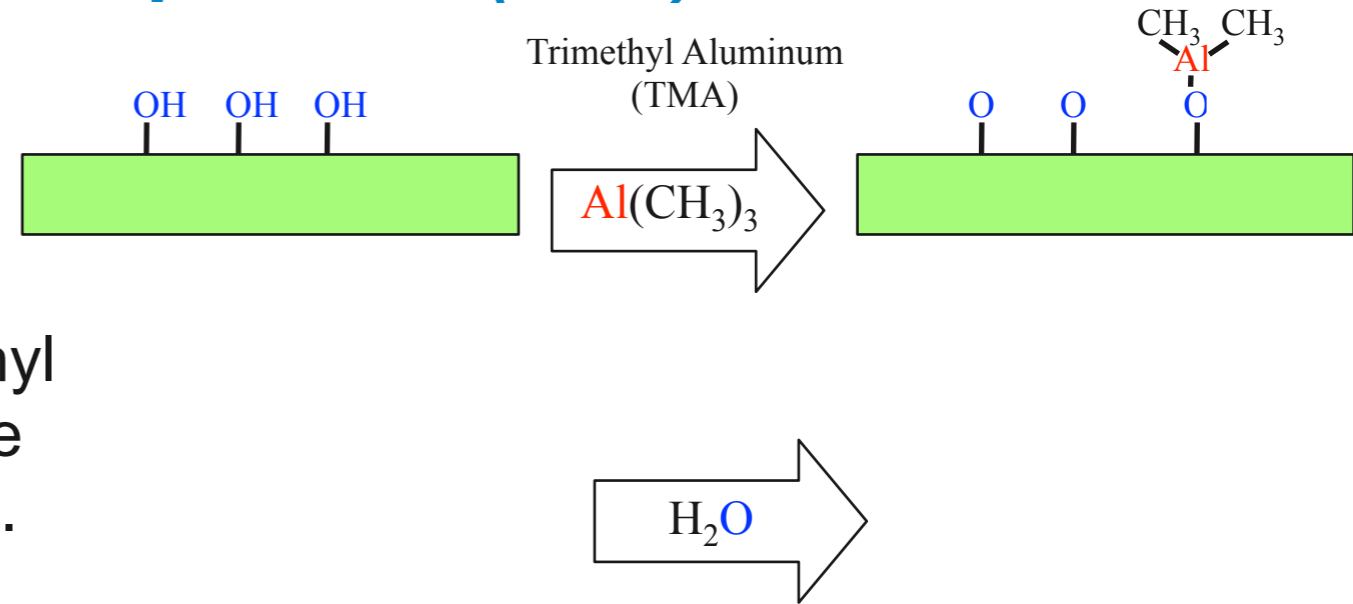
- OH on surface provide reaction sites
- Trimethyl aluminum reacts liberating methane, forms Al_2O_3 layer. Leaves methyl group inhibiting further reaction on surface
- Exposure to H_2O removes methyl group. Leaves OH sites for next reaction



Pore Activation via Atomic Layer Deposition (ALD)

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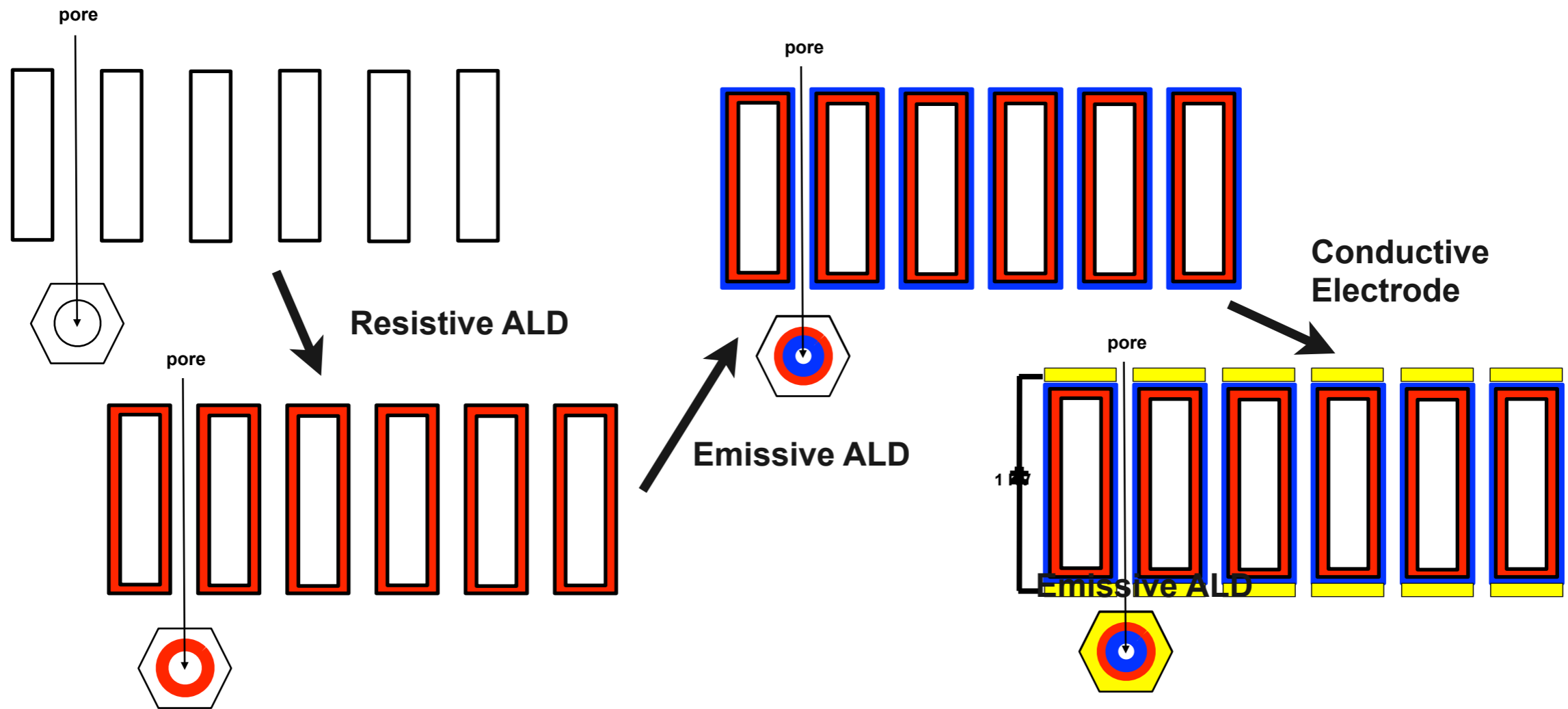
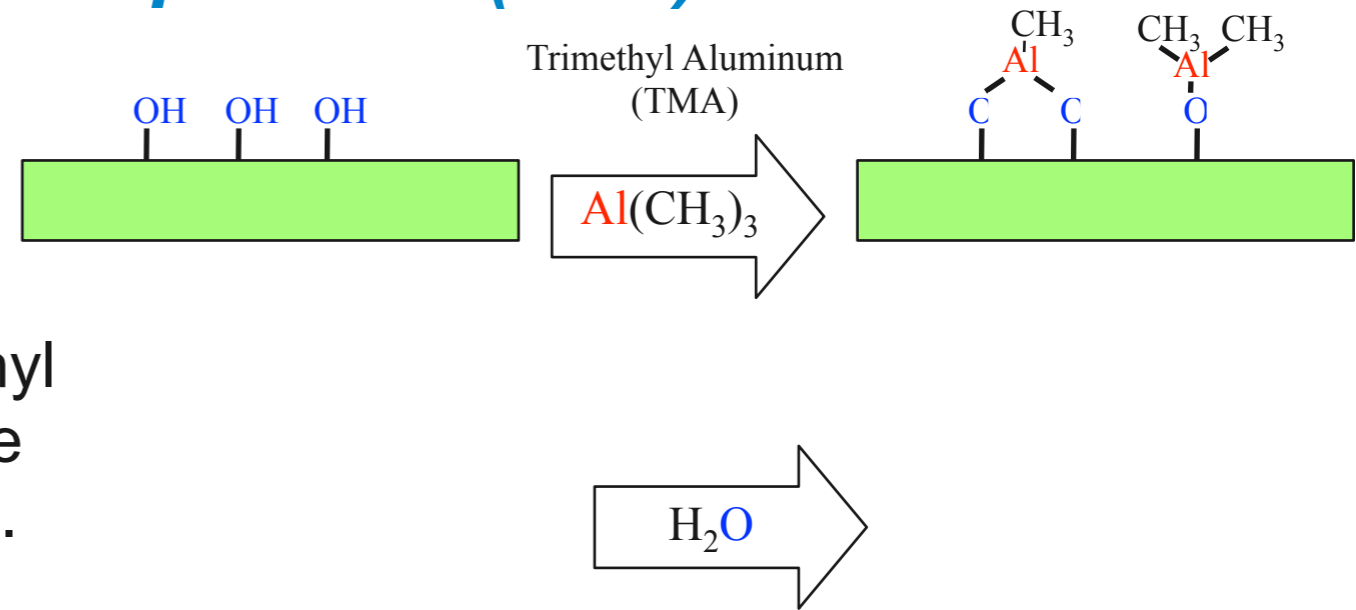
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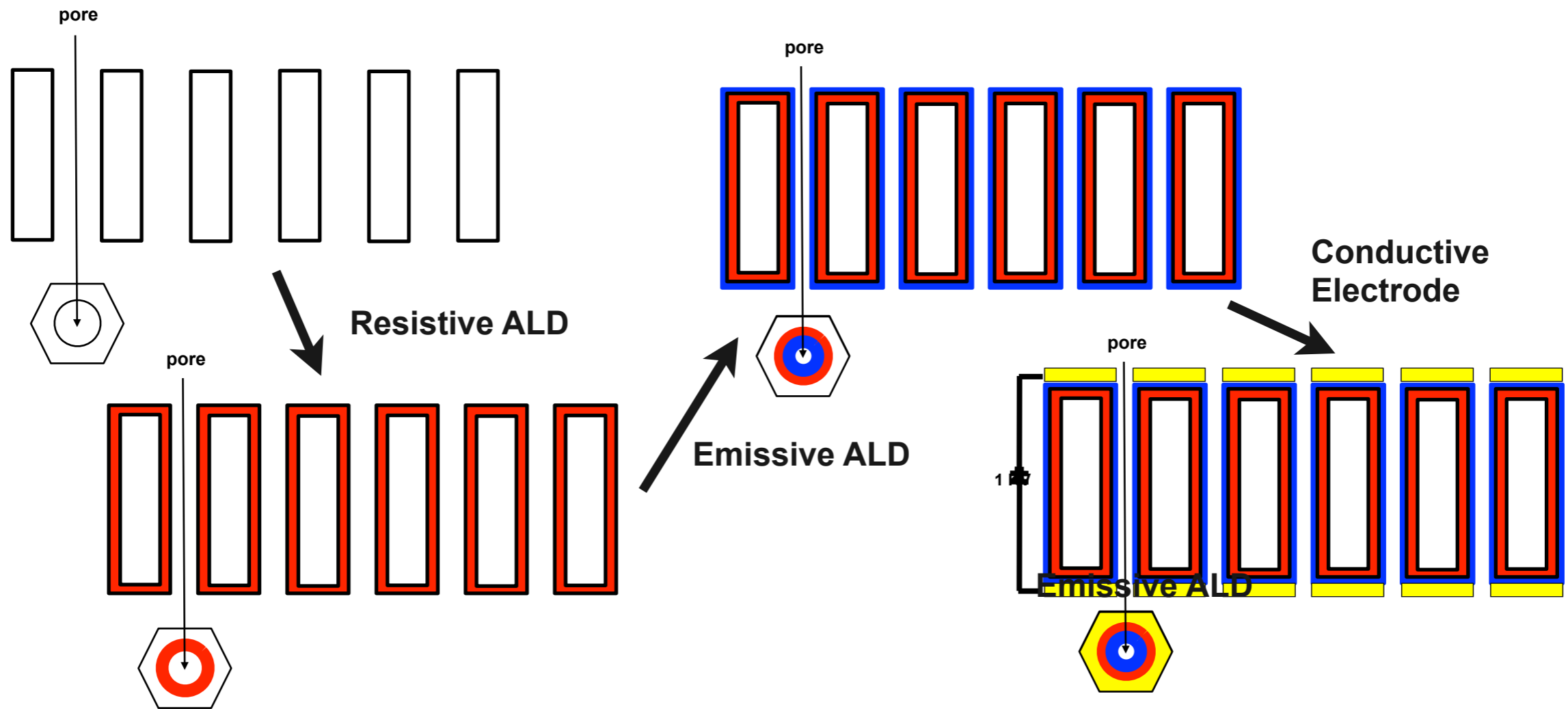
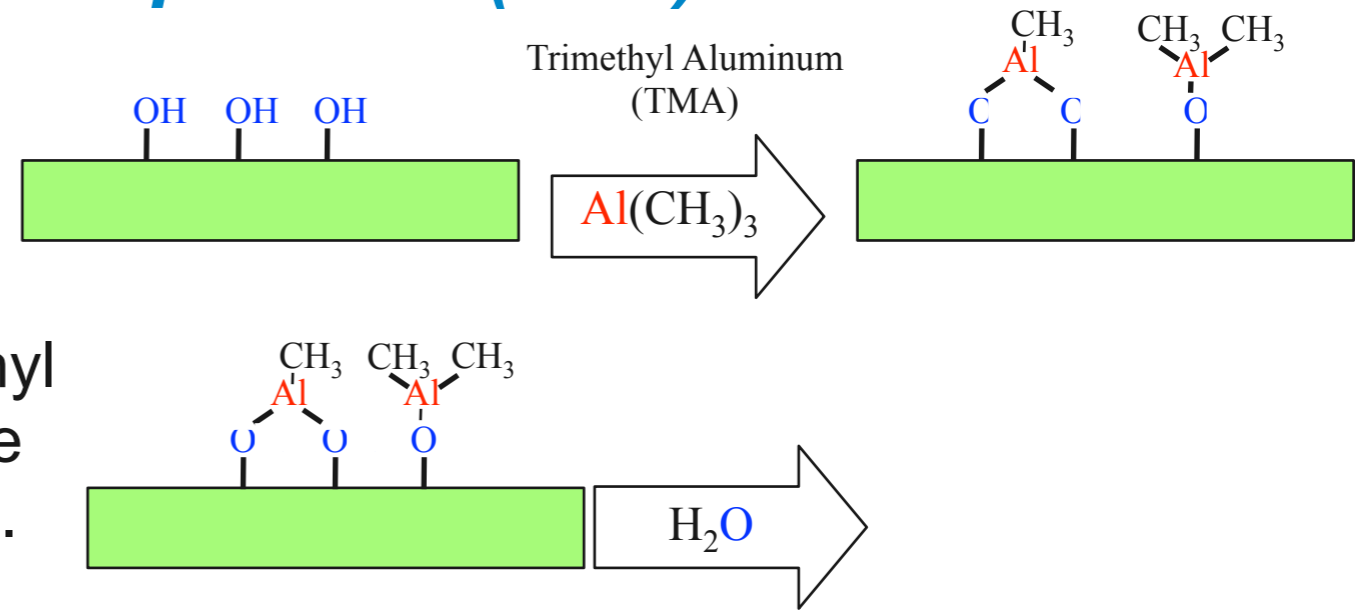
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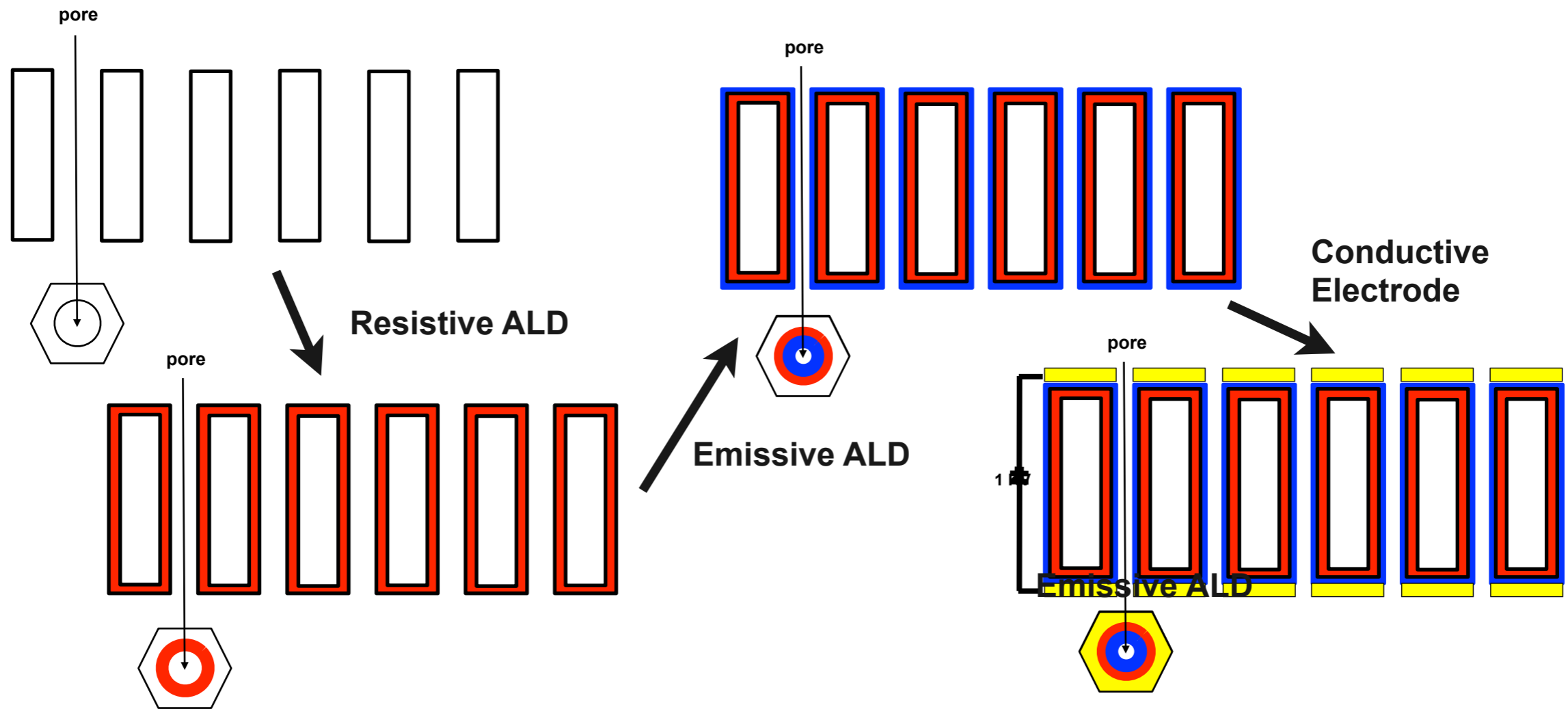
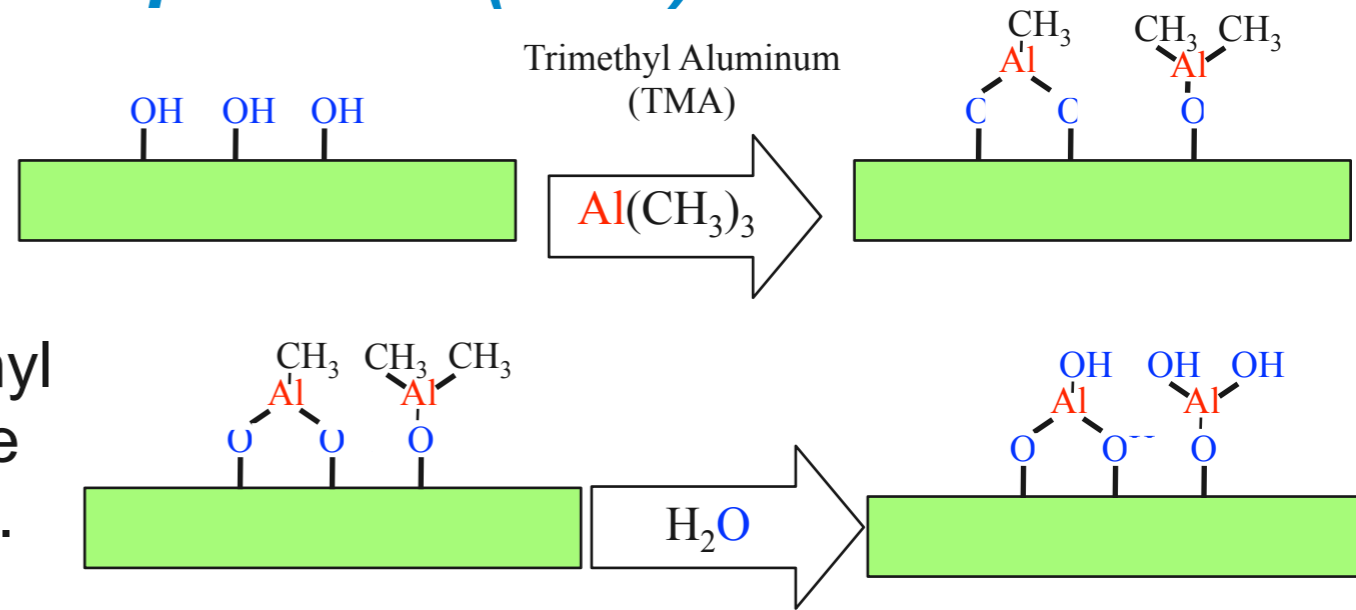
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Pore Activation via ALD -- 2



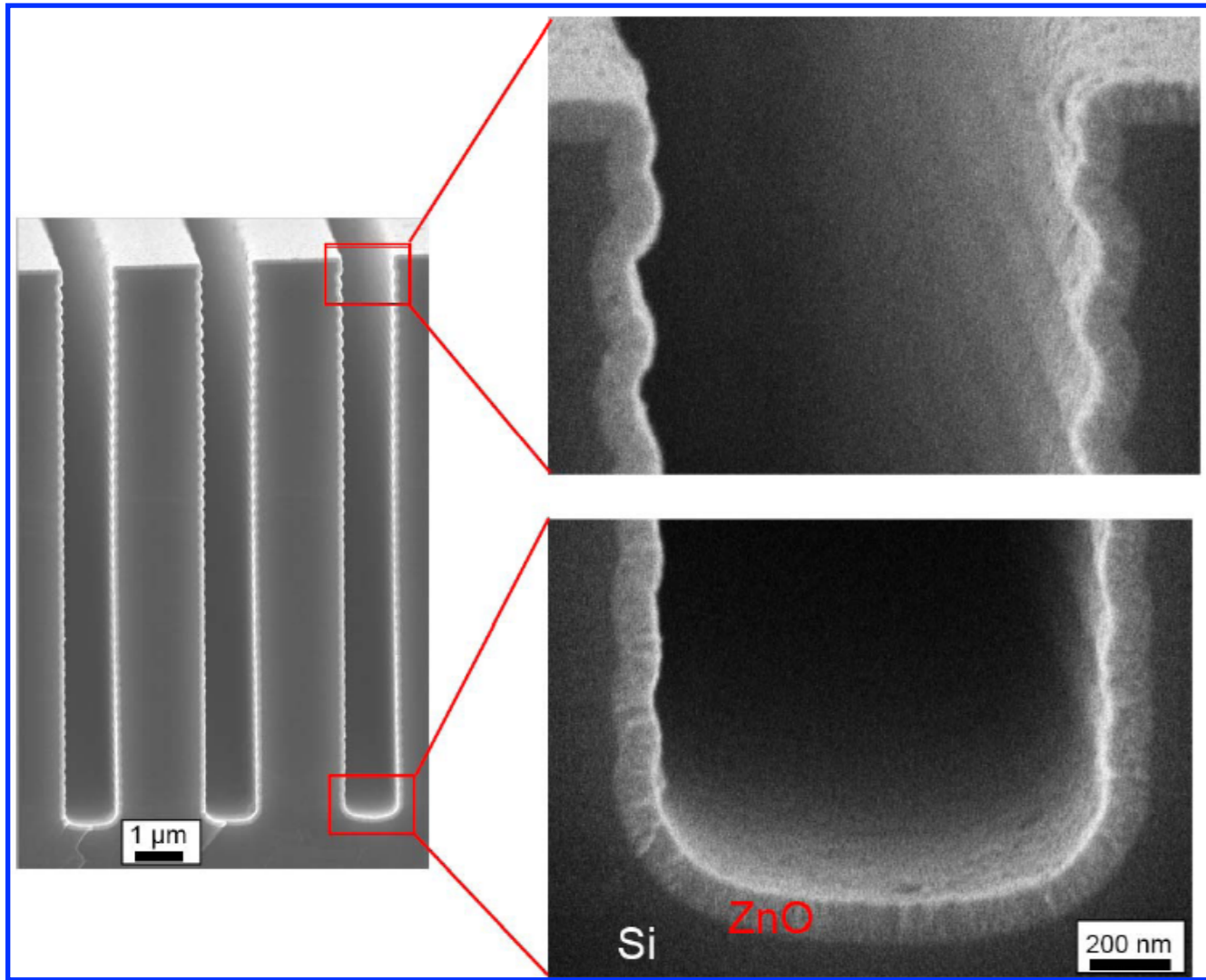
ALD Thin Film Materials

| | | | | | | | | | | | | | | | | | | |
|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|--|
| H | | | | | | | | | | | | | | | | | He | |
| Li | Be | | | | | | | | | | | B | C | N | O | F | Ne | |
| Na | Mg | | | | | | | | | | | Al | Si | P | S | Cl | Ar | |
| K | Ca | Sc | Ti | V | Cr | Mn | Fe | Co | Ni | Cu | Zn | Ga | Ge | As | Se | Br | Kr | |
| Rb | Sr | Y | Zr | Nb | Mo | Tc | Ru | Rh | Pd | Ag | Cd | In | Sn | Sb | Te | I | Xe | |
| Cs | Ba | La | Hf | Ta | W | Re | Os | Ir | Pt | Au | Hg | Tl | Pb | Bi | Po | At | Rn | |
| Fr | Ra | Lr | Rf | Db | Sg | Bh | Hs | Mt | | | | | | | | | | |
| | | | Ce | Pr | Nd | Pm | Sm | Eu | Gd | Tb | Dy | Ho | Er | Tm | Yb | Lu | | |
| | | | Th | Pa | U | Np | Pu | Am | Cm | Bk | Cf | Es | Fm | Md | No | Lw | | |

- ALD produces very uniform and continuous coating
- Footprint of apparatus is modest
- Wide variety of elements and compounds amenable to ALD

- Oxide
- Nitride
- Phosphide/Arsenide
- Sulphide/Selenide/Telluride
- Element
- Carbide
- Fluoride
- Dopant
- Mixed Oxide

Pore Activation via ALD -- 2



ALD Thin Film Materials

| | | | | | | | | | | | | | | | | | | | | | |
|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|--|--|----|----|
| H | | | | | | | | | | | | | | | | | | | | He | |
| Li | Be | | | | | | | | | | | | | | | | | | | | Ne |
| Na | Mg | | | | | | | | | | | | | | | | | | | | Ar |
| K | Ca | Sc | Ti | V | Cr | Mn | Fe | Co | Ni | Cu | Zn | Ga | Ge | As | Se | Br | Kr | | | | |
| Rb | Sr | Y | Zr | Nb | Mo | Tc | Ru | Rh | Pd | Ag | Cd | In | Sn | Sb | Te | I | Xe | | | | |
| Cs | Ba | La | Hf | Ta | W | Re | Os | Ir | Pt | Au | Hg | Tl | Pb | Bi | Po | At | Rn | | | | |
| Fr | Ra | Lr | Rf | Db | Sg | Bh | Hs | Mt | | | | | | | | | | | | | |
| | | | Ce | Pr | Nd | Pm | Sm | Eu | Gd | Tb | Dy | Ho | Er | Tm | Yb | Lu | | | | | |
| | | | Th | Pa | U | Np | Pu | Am | Cm | Bk | Cf | Es | Fm | Md | No | Lw | | | | | |

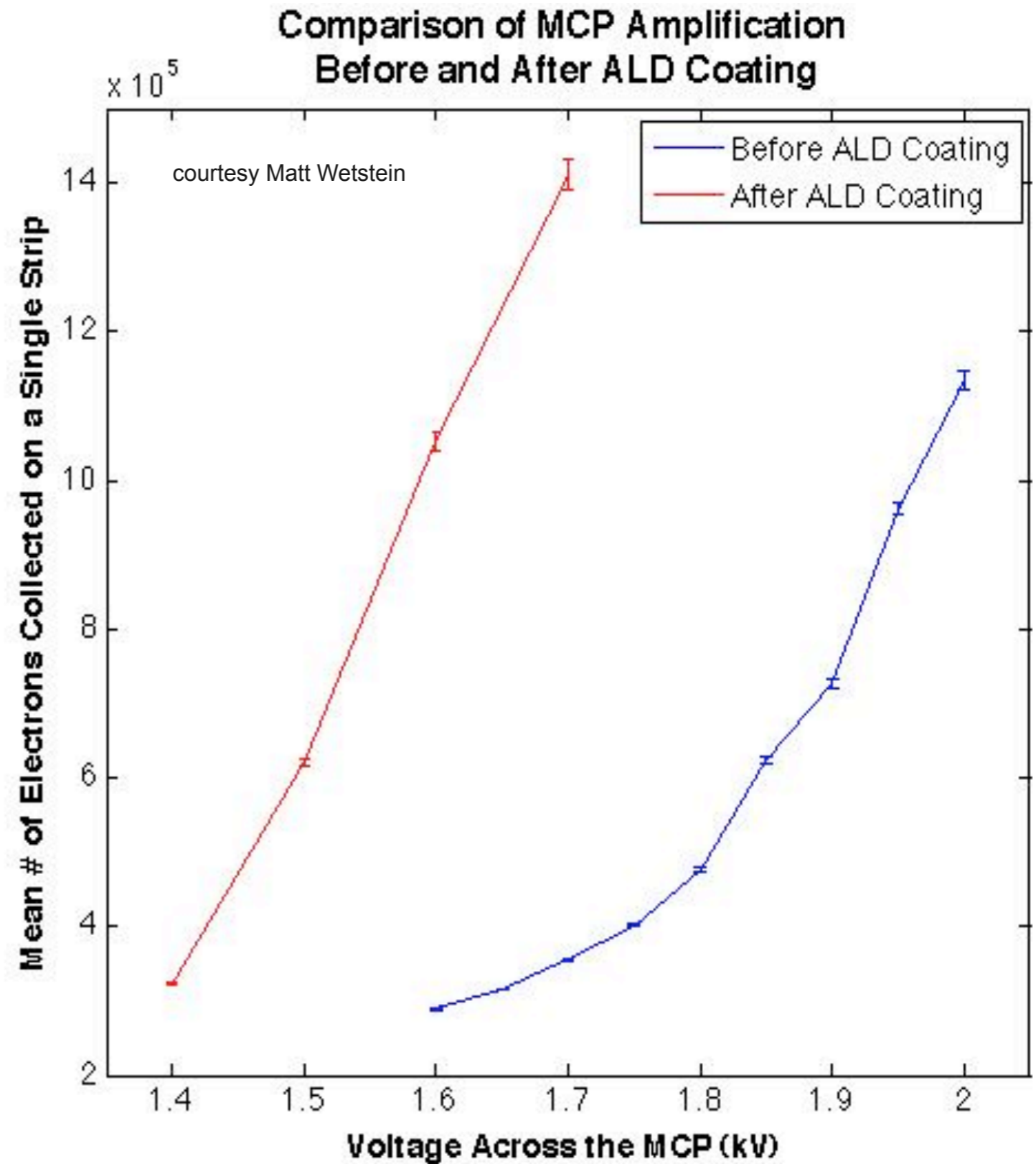
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- Element
- Carbide
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- Dopant
- Mixed Oxide

Observation of Gain with ALD Coating

Early Test: Coat Pb-Glass
Photonis MCP with Al_2O_3 ;
emissive coating only

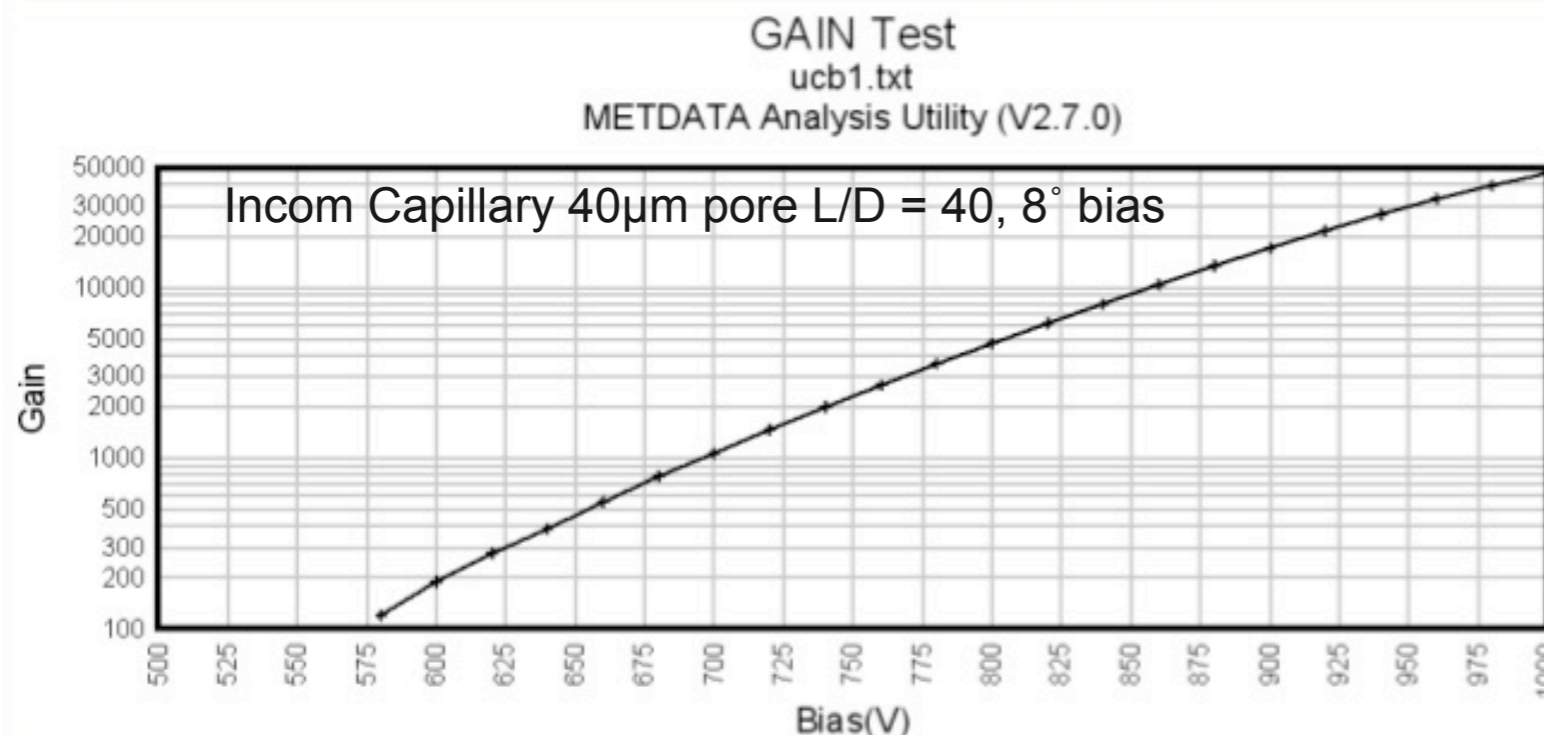
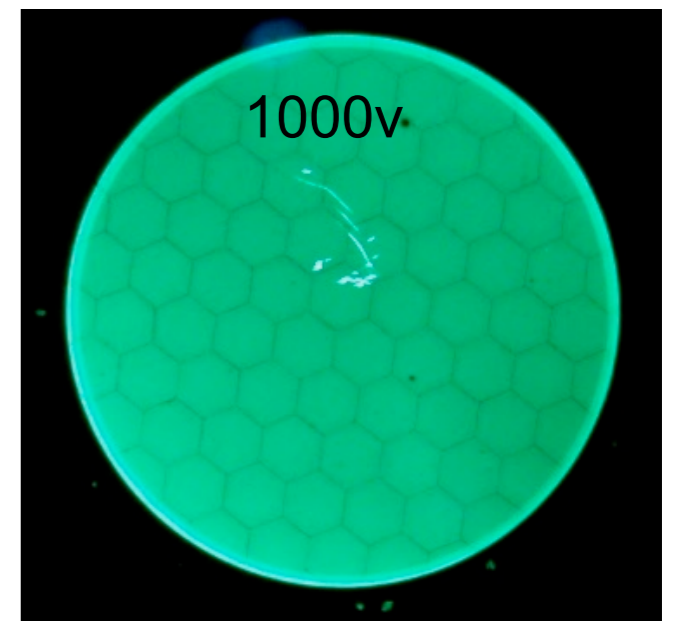
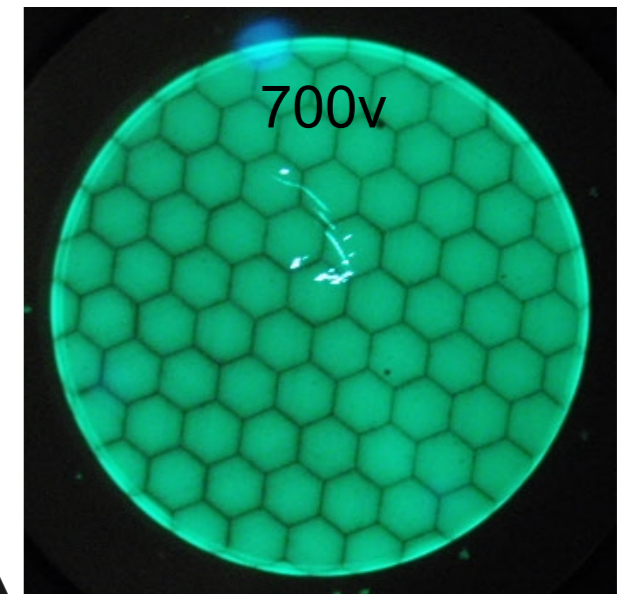
Observe increased gain
lower voltage for equivalent gain



Observation of Gain with ALD Coating -- Arradiance/SSL

- Incom substrate, 40 μ m pore, L/D = 40, 8° bias
- Resistive + Secondary Emissive + Electrode @ Arradiance
- Tested using phosphor with UV light at UC Berkeley - SSL
- No light \rightarrow black, UV light \rightarrow bright image
- Gain measured at Arradiance below

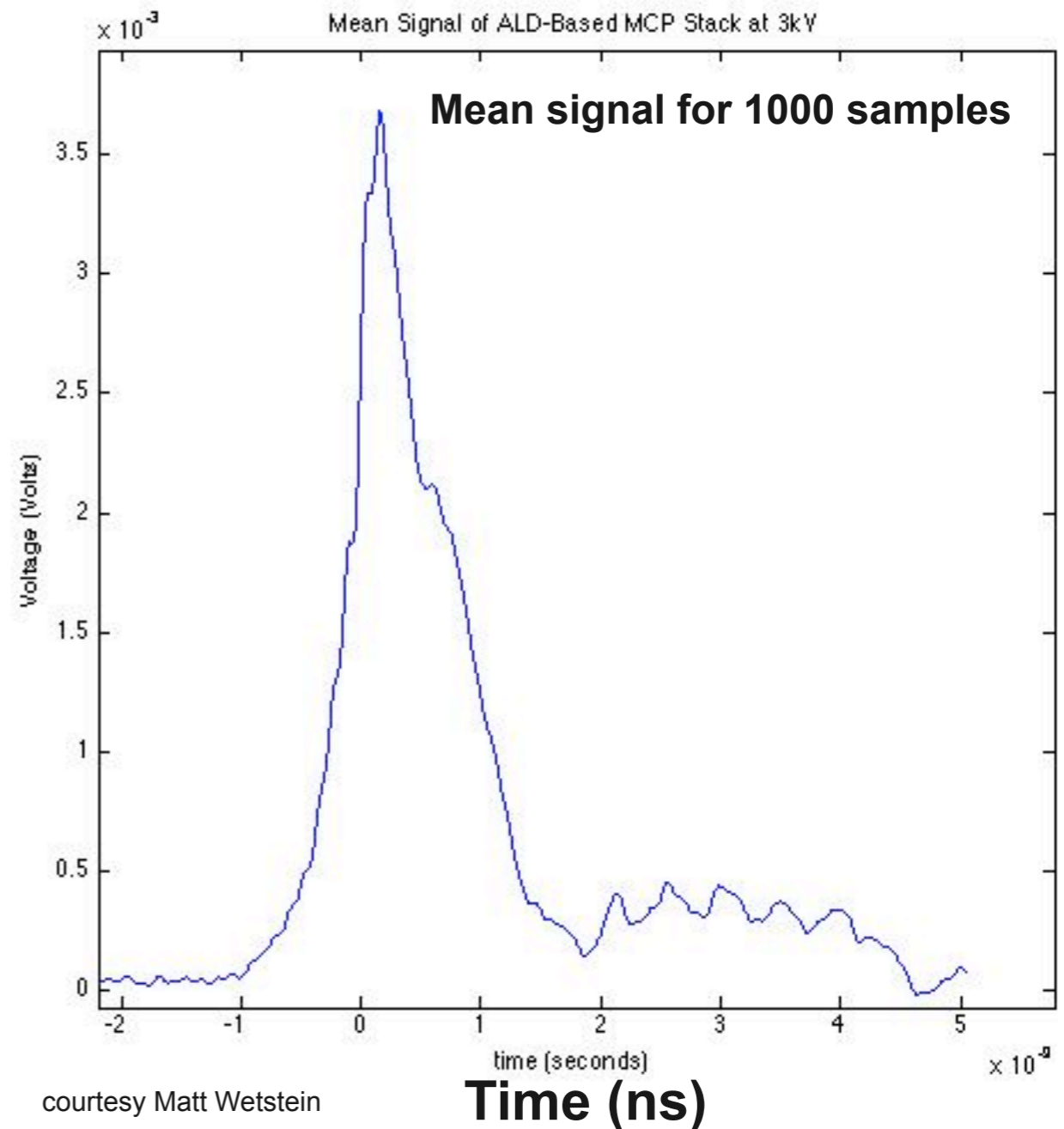
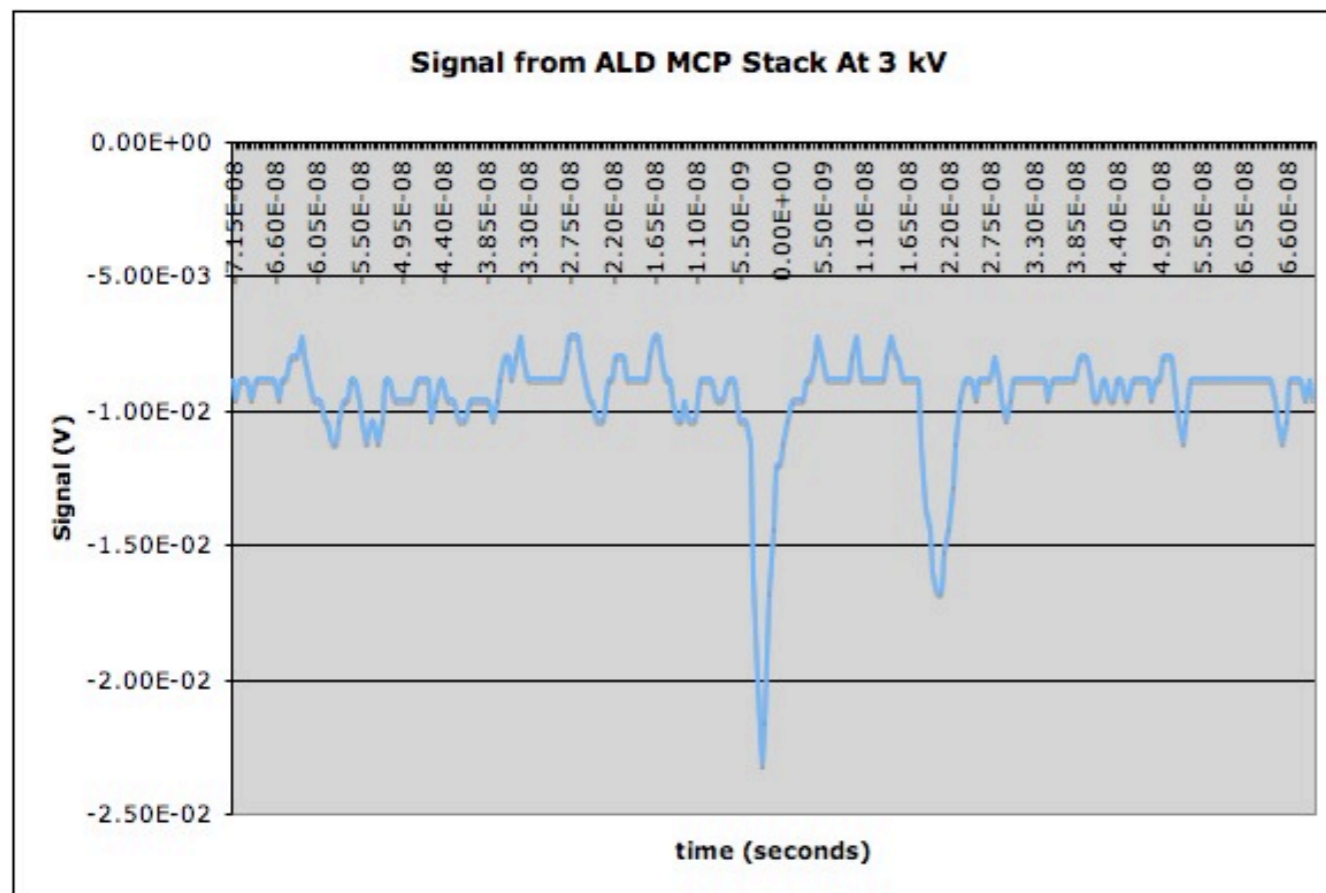
It Works!



Gain measured at Arradiance, Inc.
50,000 @ 1000V

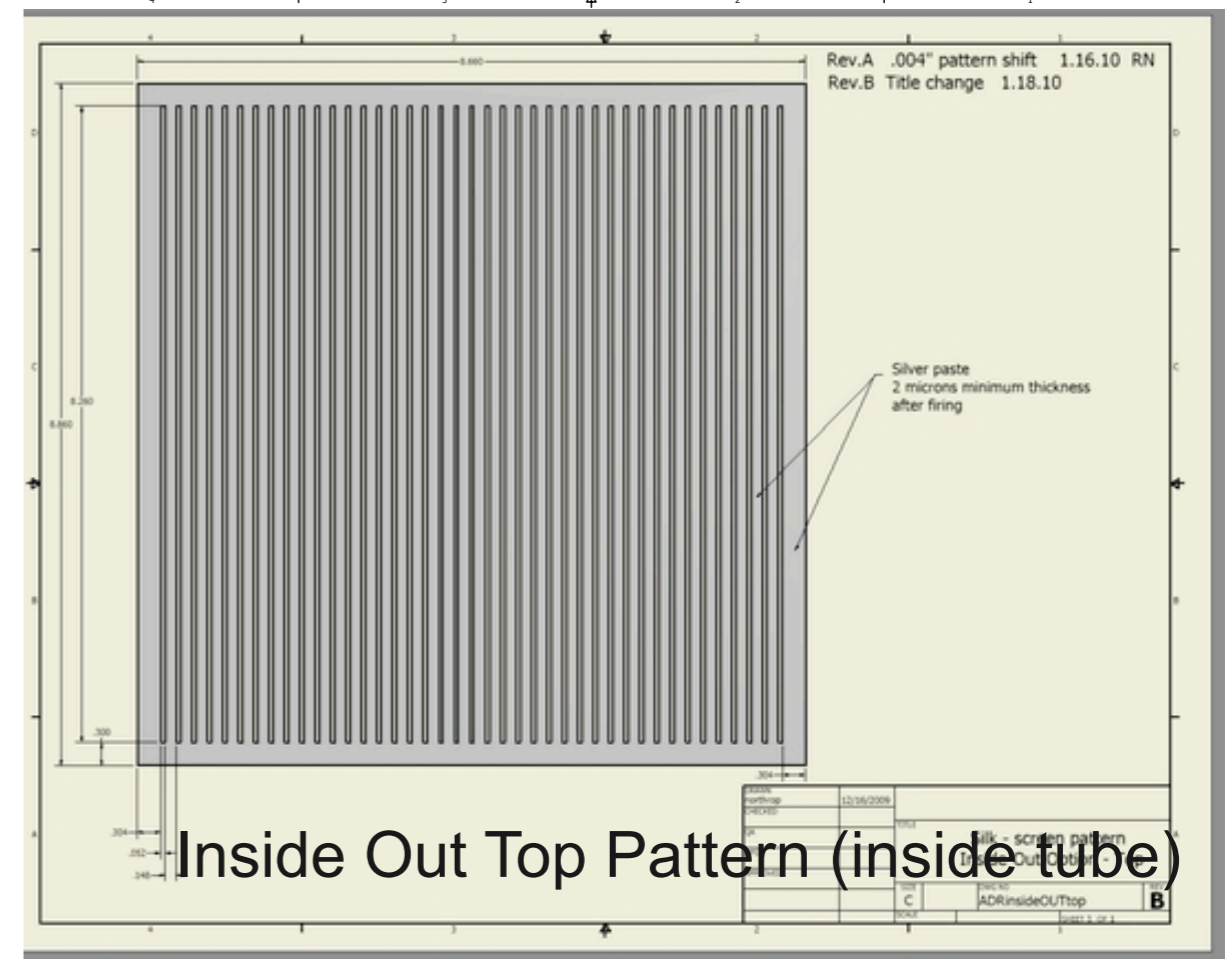
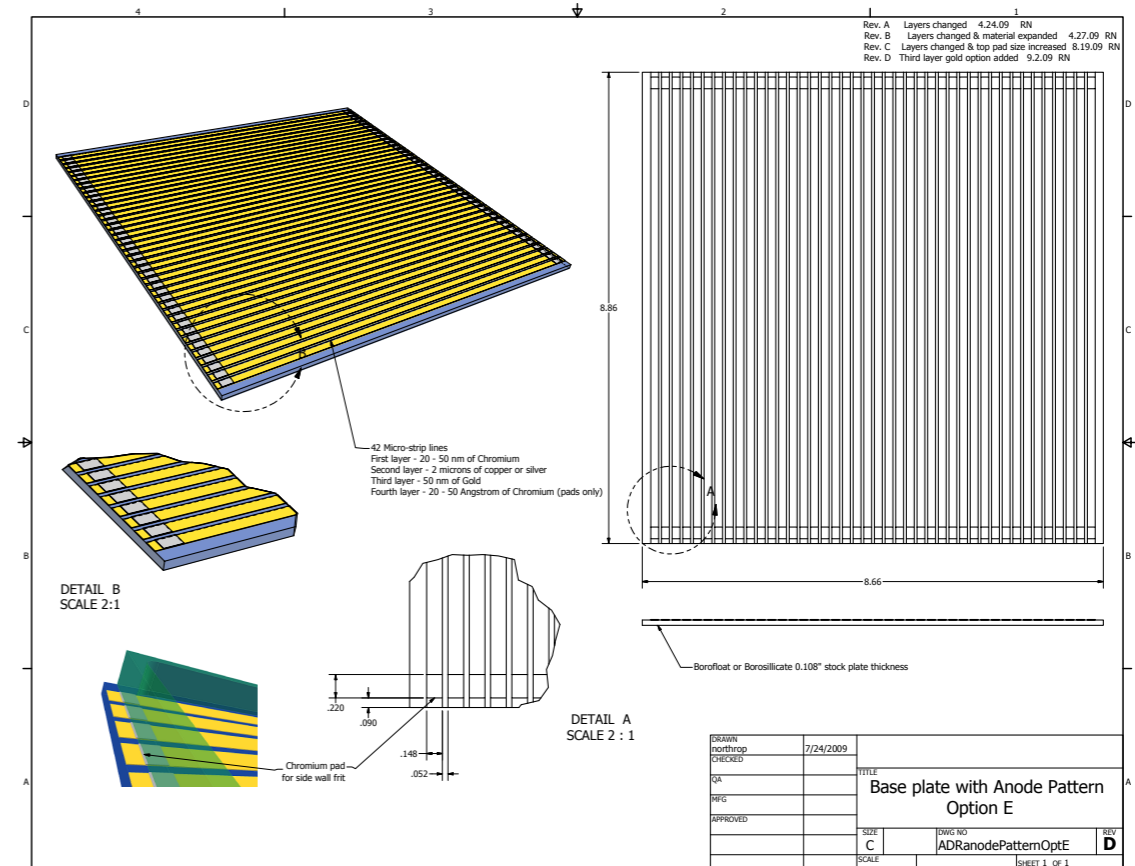
Observation of Gain with ALD Coating -- Argonne

- Incom 40 μ m pore, L/D = 40, 8° bias
- ALD resistive layer ZnO, emissive Al₂O
- Gold electrode
- Observe gain multiplication @ 3kV



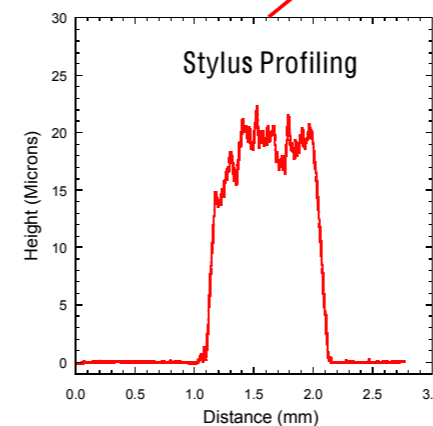
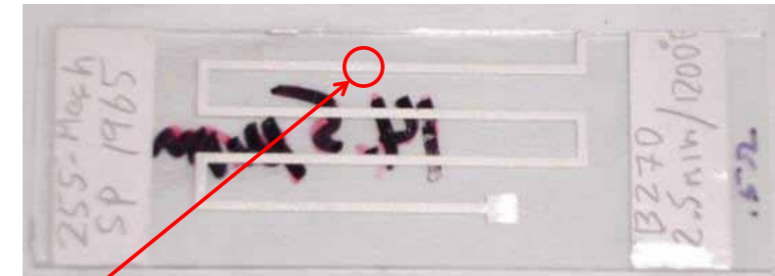
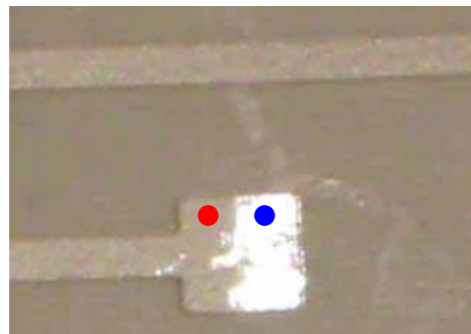
Anode Design

- Focus on anode strip line design for precision timing application
- Pursuing several alternatives for metal on glass: sputtering, evaporation, silk screening
- Anode materials
 - Chromium, Nichrome, Titanium base layer for adherence to glass
 - Copper, Silver for signal transmission
 - Gold overcoat to prevent oxidation
 - Chromium pads for sidewall-to-glass seal
- Also studying simple silk screen with silver paste. Bond sidewall to silver??
- Sidewall/bottom plate bonding alternatives
 - glass frit
 - direct metal-to-glass bond
- Studying “Inside Out” Alternative to detect image charge signal with external strip lines
- Initial solution likely to be ceramic tray with plated through vias (SSL standard)

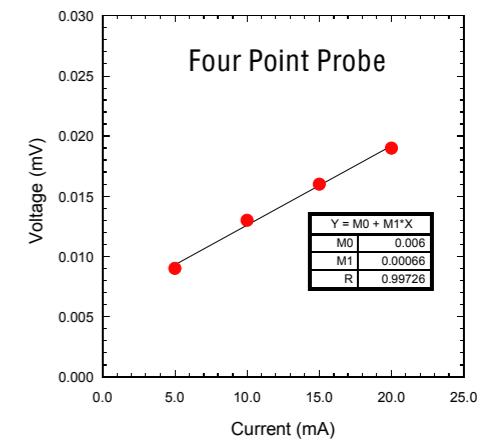


Silver Paste Silk Screening

- Studying viability of silk screening anode pattern with silver paste
 - several groups involved: Ferro, Argonne glass shop, Argonne HEP
- Initial sample from Ferro characterized by Argonne ALD group (Jeff Elam)



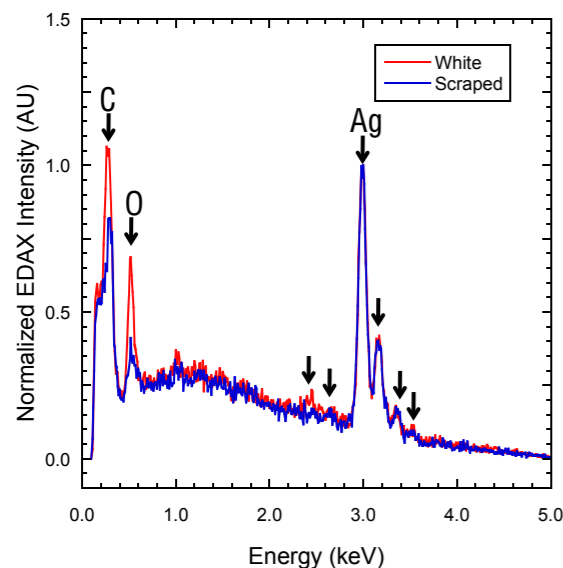
Ag thickness, $t=18.5 \mu\text{m}$
Ag roughness : RMS=2 μm



Sheet resistance $R_s=4.532(V/I)=3.00e^{-3} \Omega/\square$

- Resistivity $\rho=R_s t=5.5 \mu\Omega\text{cm}$
- pure Ag, $\rho=1.6 \mu\Omega\text{cm}$ (higher for thin films), pure AgO=60 Ωcm
- Resistivity consistent with Ag thin film

courtesy of Jeff Elam



| | Atomic % | | | |
|---------|----------|----|----|------|
| | C | O | Ag | O/Ag |
| White | 60 | 34 | 6 | 5.7 |
| Scraped | 64 | 25 | 10 | 2.5 |

- both regions show significant C, O
- white area shows higher O/Ag
- EDAX signals might represent only near-surface region
- Ag_2O is soluble in acid – tried phosphoric, sulfuric, and acetic acid on white region – it didn't dissolve.

Mechanical Assembly -- 1

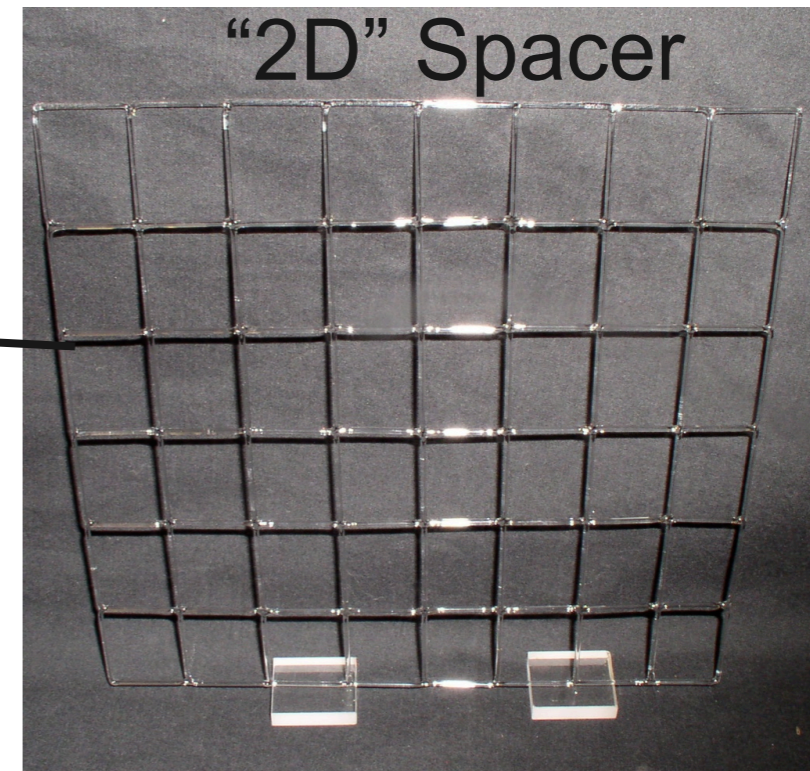
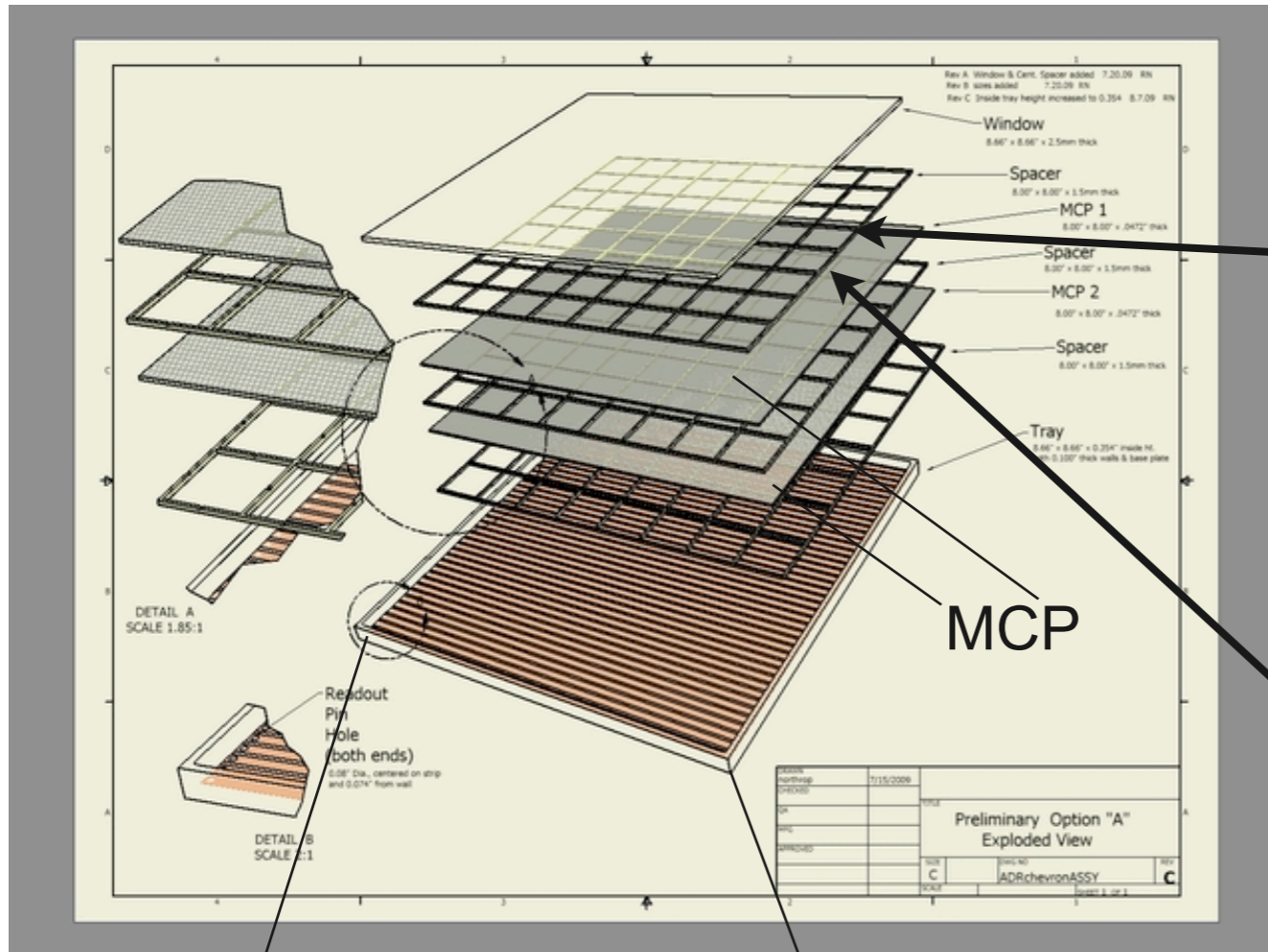
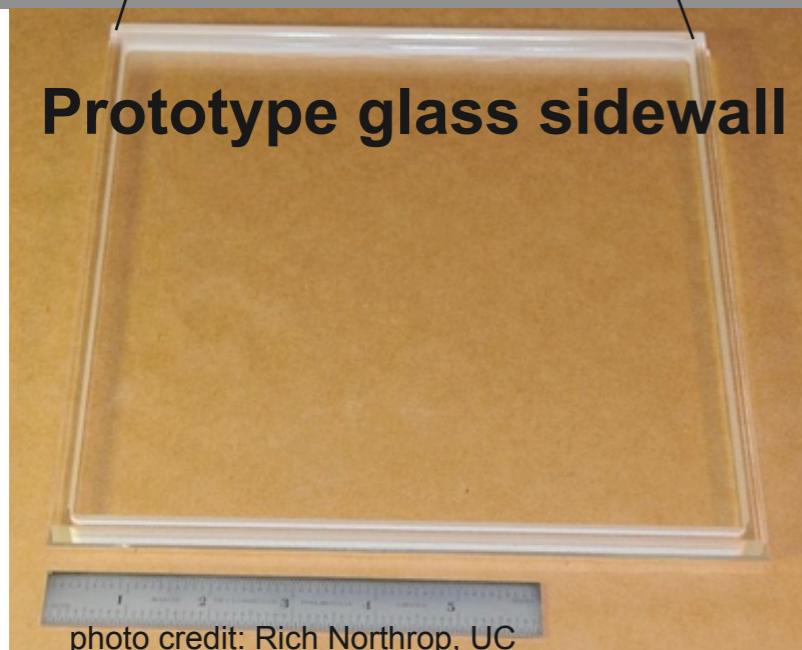
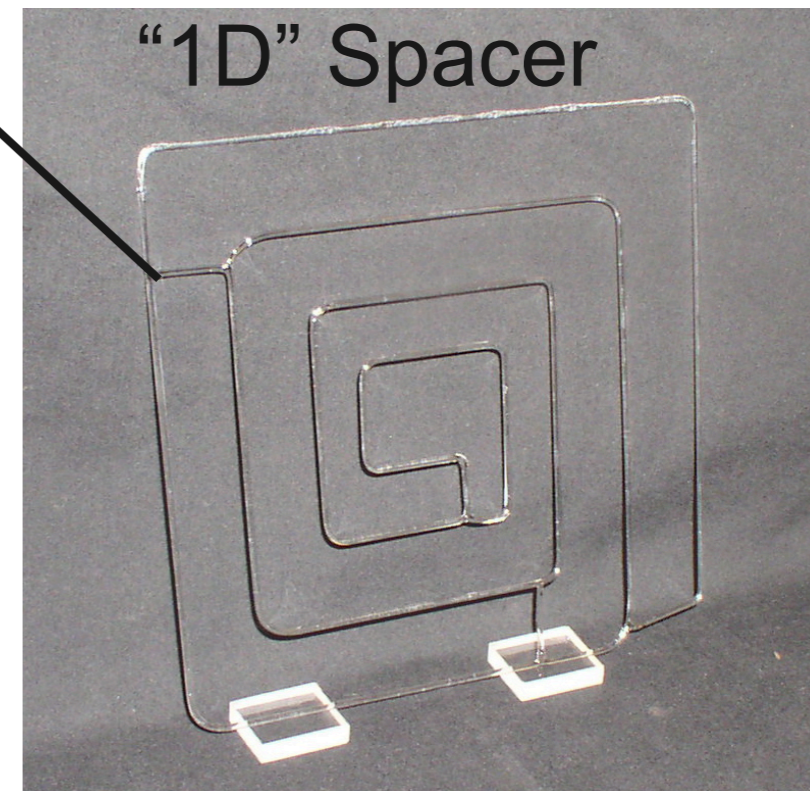


photo credit: Joe Gregar, Argonne

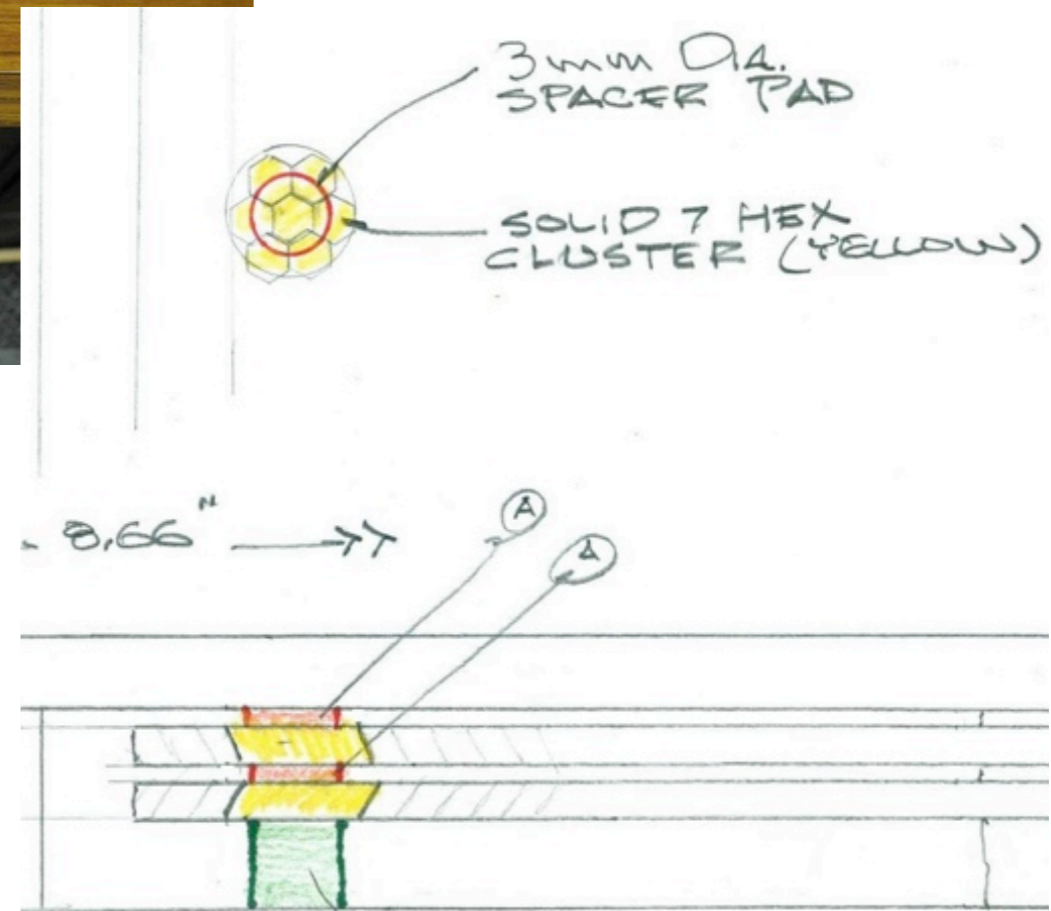


Mechanical Assembly -- 2



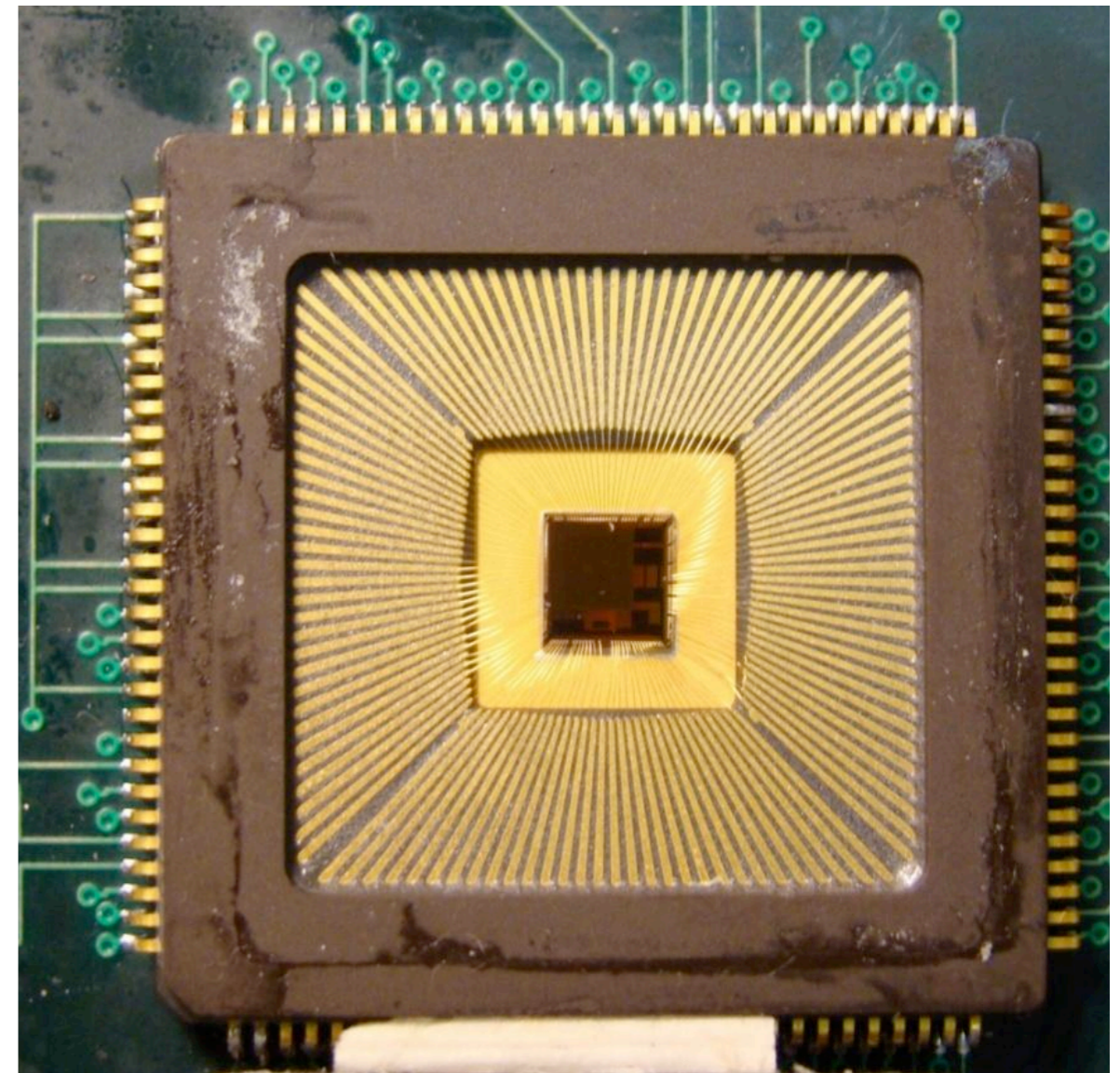
Alternative spacer design:

- Use button spacers arranged in grid
- Glass substrate has solid “multis” inserted as “lily pads”
- Buttons for each layer form columns to provide continuous solid support



Picosecond Timing Readout ASIC

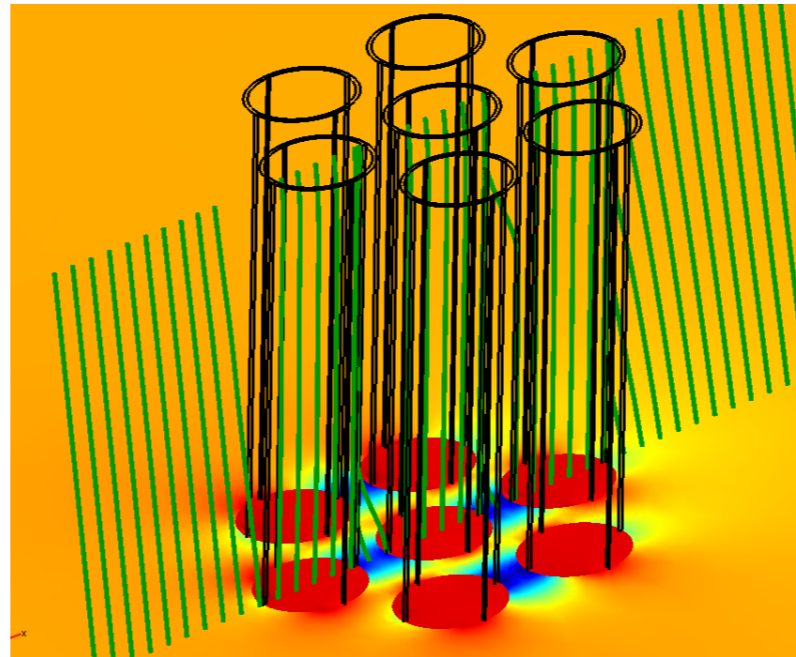
- Univs. Chicago/Hawaii ASIC design for readout using switched capacitor array in 130nm CMOS
- 1st round chips delivered in Oct, 2009
 - 4 channels of full sampling
 - 10-15 Gsamples/s
 - 256 cells @ < 100ps/cell
 - 1-2 GHz bandwidth, 50Ω
- Have tested:
 - DC power vs. bias
 - Sampling cell response vs input
 - ADC's comparator
 - Leakage
 - Digital readout
- AC testing in preparation
- Next design underway with many improvements: input trigger disc., phase lock, higher bandwidth, increased sampling rate,...
 - Likely submission May, 2010



Simulation Work

- Simulation studies being performed at Argonne, Muons, Inc., Arradiance
- Example: E-Field direction in pore done by Sergey Antipov, Argonne
- Many other simulations completed or underway
 - Saturation effects
 - Secondary electron emission
 - End spoiling effect on E-field
 - Noise factor
 - Charge relaxation time

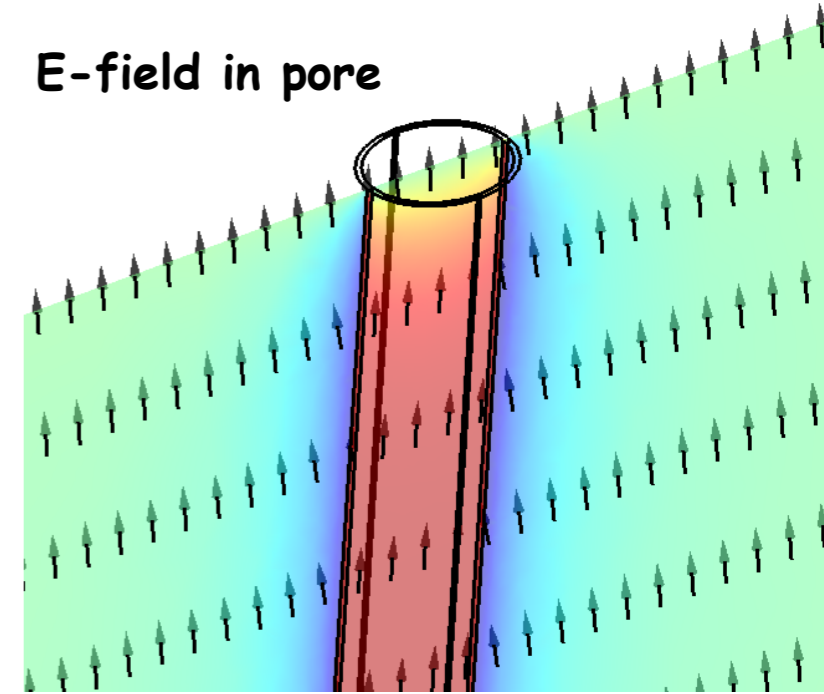
E-field Angle $\sim 8^\circ$,
field aligns along the pore



Color: Angle= $\text{Atan}(E_x/E_z)$
Streamlines in cross section
- electric field

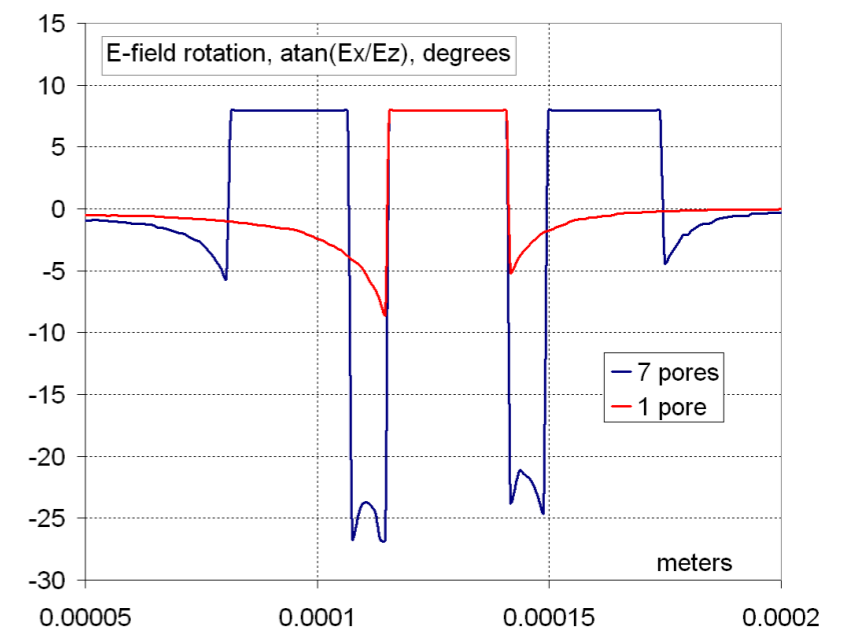
courtesy of Sergey Antipov

E-field in pore



Color: Angle= $\text{Atan}(E_x/E_z)$
Arrows: Electric field

E-field inside 7 pores



Summary

- Large Area Photodetector Development project has been active for 6 months; preceded by 2+ years work with Photonis Planacon and commercial amp-disc-TAC for picosecond timing development
- A lot of progress in 6 months; many studies & developments running in parallel
 - Demonstrated gain with ALD coated glass substrate MCP
 - Characterization facilities in place and producing results
 - Design of anode and mechanical assembly is maturing; some definite results in near future
- Expertise working on project encompasses many scientific disciplines: Material Science, Chemistry, Surface Physics, HEP, Forefront electronics, Vacuum Technology
 - Seems to be working amazingly well
 - Have a number of talented, enthusiastic young scientists producing good results
- Challenges exist in the present and future; work to date is basis for expecting success

Many topics, results neglected to keep within time.

You are invited to browse a wealth of information on our web site:

psec.uchicago.edu